Common Mode Filter with ESD Protection

Functional Description

The EMI4183MU is an integrated common mode filter providing both ESD protection and EMI filtering for high speed digital serial interfaces such as MIPI D-PHY.

The EMI4183MU provides protection for three differential data line pairs in a small RoHS-compliant UDFN16 package.

Features

- Highly Integrated Common Mode Filter (CMF) with ESD Protection provides protection and EMI reduction for systems using High Speed Serial Data Lines with cost and space savings over discrete solutions
- Large Differential Mode Bandwidth with Cutoff Frequency > 2 GHz
- High Common Mode Stop Band Attenuation: >25 dB at 700 MHz, >30 dB at 800 MHz
- Provides ESD Protection to IEC61000-4-2 Level 4, ±15 kV Contact Discharge
- Low Channel Input Capacitance Provides Superior Impedance Matching Performance
- Low Profile Package with Small Footprint in UDFN16 2 x 4 mm Pb-Free Package
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

• MIPI D-PHY (CSI-2, DSI, etc) in Mobile Phones and Digital Still Cameras

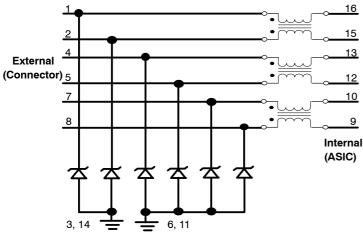


Figure 1. EMI4183MU Electrical Schematic



ON Semiconductor®

http://onsemi.com



MARKING DIAGRAMS



UDFN16 CASE 517CK

U3 = Specific Device Code

M = Date Code

= Pb-Free Package

(*Note: Microdot may be in either location)

PIN CONNECTIONS

| | 16 | Out_1+ | | | | | |
|------------|------------------|--|--|--|--|--|--|
| 2 | 15 | Out_1- | | | | | |
| 3 | 14 | GND | | | | | |
| 1 | 13 | Out_2+ | | | | | |
| 5 | 12 | Out_2- | | | | | |
| 6 | 11 | GND | | | | | |
| 7 | 10 | Out_3+ | | | | | |
| 8 | 9 | Out_3- | | | | | |
| (Top View) | | | | | | | |
| | 3 5 5 7 | 2 15 3 14 4 13 5 12 6 11 7 10 | | | | | |

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|--------------|---------------------|-----------------------|
| EMI4183MUTAG | UDFN16 (Pb-Free) | 3000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PIN FUNCTION DESCRIPTION

| Pin Name | Pin No. | Туре | Description |
|----------|---------|------|--|
| ln_1+ | 1 | I/O | CMF Channel 1+ to Connector (External) |
| ln_1- | 2 | I/O | CMF Channel 1- to Connector (External) |
| Out_1+ | 16 | I/O | CMF Channel 1+ to ASIC (Internal) |
| Out_1- | 15 | I/O | CMF Channel 1- to ASIC (Internal) |
| In_2+ | 4 | I/O | CMF Channel 2+ to Connector (External) |
| In_2- | 5 | I/O | CMF Channel 2- to Connector (External) |
| Out_2+ | 13 | I/O | CMF Channel 2+ to ASIC (Internal) |
| Out_2- | 12 | I/O | CMF Channel 2- to ASIC (Internal) |
| In_3+ | 7 | I/O | CMF Channel 3+ to Connector (External) |
| In_3- | 8 | I/O | CMF Channel 3- to Connector (External) |
| Out_3+ | 10 | I/O | CMF Channel 3+ to ASIC (Internal) |
| Out_3- | 9 | I/O | CMF Channel 3- to ASIC (Internal) |
| GND | 3, 14 | GND | Ground |
| GND | 6, 11 | GND | Ground |

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|-------------------|-------------|------|
| Operating Temperature Range | T _{OP} | -40 to +85 | °C |
| Storage Temperature Range | T _{STG} | -65 to +150 | °C |
| Maximum Lead Temperature for Soldering Purposes (1/8" from Case for 10 seconds) | TL | 260 | °C |
| DC Current per Line | I _{LINE} | 100 | mA |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Unit |
|--------------------|---|--|-----------|-----------------------|-----|-------------|
| I _{LEAK} | Channel Leakage Current | T _A = 25°C, V _{IN} = 5 V, GND = 0 V | | | 1.0 | μΑ |
| V _F | Channel Negative Voltage | T _A = 25°C, I _F = 10 mA | 0.1 | | 1.5 | V |
| C _{IN} | Channel Input Capacitance to Ground (Pins 1,2,4,5,7,8 to Pins 3,6,11,14) | $T_A = 25^{\circ}C$, At 1 MHz, GND = 0 V, $V_{IN} = 1.65$ V | | 0.8 | 1.3 | pF |
| R _{CH} | Channel Resistance (Pins 1–16, 2–15, 4–13, 5–12, 7–10 & 8–9) | | | 8.0 | | Ω |
| f _{3dB} | Differential Mode Cut-off Frequency | 50 Ω Source and Load Termination | | 2.0 | | GHz |
| F _{atten} | Common Mode Stop Band Attenuation | @ 800 MHz | | 30 | | dB |
| V _{ESD} | In-system ESD Withstand Voltage a) Contact discharge per IEC 61000-4-2 standard, Level 4 (External Pins) b) Contact discharge per IEC 61000-4-2 standard, Level 1 (Internal Pins) | (Notes 1 and 2) | ±15 ±2 | | | kV |
| V _{CL} | TLP Clamping Voltage (See Figure 12) | Forward Ipp = $8 A$ Forward Ipp = $16 A$ Forward Ipp = $-8 A$ Forward Ipp = $-16 A$ | | 12 18 -6 -12 | | V V V |
| R _{DYN} | Dynamic Resistance Positive Transients Negative Transients | T_A = 25°C, I_{PP} = 1 A, t_P = 8/20 μ s Any I/O pin to Ground; (Notes 1 and 3) | | 1.36 0.6 | | |
| V_{RWM} | Reverse Working Voltage | (Note 3) | | | 5.0 | V |
| V_{BR} | Breakdown Voltage | I _T = 1 mA; (Note 4) | 5.6 | | 9.0 | V |

Standard IEC61000–4–2 with C_{Discharge} = 150 pF, R_{Discharge} = 330, GND grounded.
 These measurements performed with no external capacitor.
 TVS devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level.
 V_{BR} is measured at pulse test current I_T.

TYPICAL CHARACTERISTICS

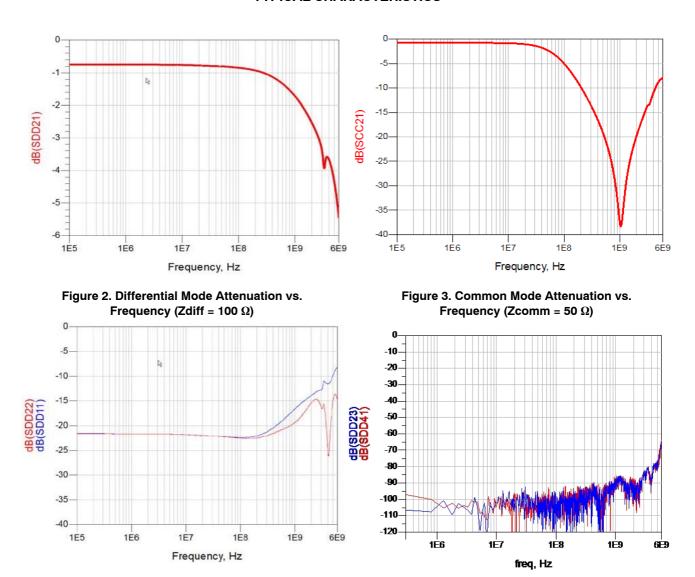


Figure 4. Differential Return Loss vs. Frequency (Zdiff = 100 Ω)

Figure 5. Differential Inter-Lane Cross-Coupling

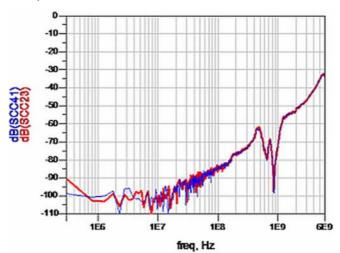


Figure 6. Common Mode Inter-Lane Cross-Coupling

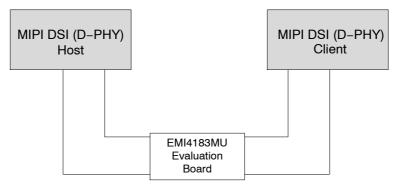


Figure 7. MIPI D-PHY LP Mode Test Setup



Figure 8. EMI4183MU MIPI D-PHY LP Mode Measured Results

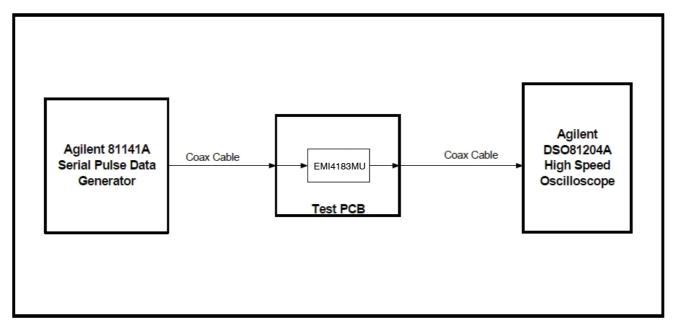


Figure 9. EMI4183MU Eye Diagram Test Setup



Figure 10. EMI4183MU Measured Eye Diagram @ 3.4Gbps (EVB through on left, EVB with EMI4183MU on right)

Transmission Line Pulse (TLP) Measurements

Transmission Line Pulse (TLP) provides current versus voltage (I-V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 11. TLP I-V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10 s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 12 where an 8 kV IEC61000-4-2 current waveform is compared with TLP current pulses at 8 and 16 A. A TLP curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels. Typical TLP I-V curves for the EMI4183MU are shown in Figure 13.

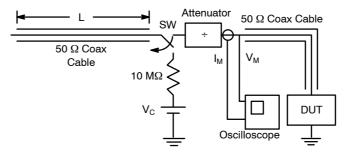


Figure 11. Simplified Schematic of a Typical TLP System

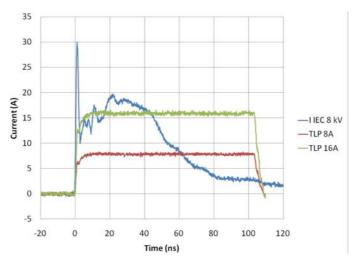
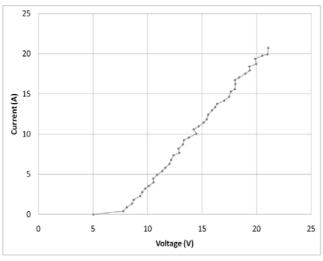


Figure 12. Comparison Between 8 kV IEC61000-4-2 and 8 A and 16 A TLP Waveforms



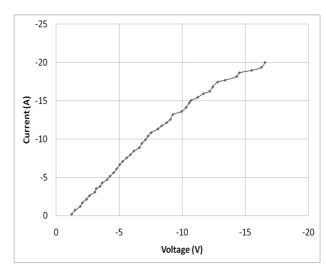


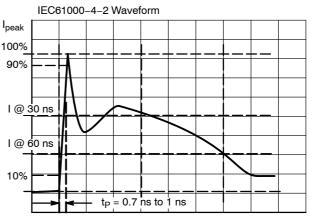
Figure 13. Positive and Negative TLP Waveforms

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to On Semiconductor Application Notes AND8307/D and AND8308/D.

IEC61000-4-2 Spec.

| Level | Test Voltage (kV) | First Peak Current (A) | Current at 30 ns (A) | Current at 60 ns (A) |
|-------|-------------------------|------------------------------|-------------------------|-------------------------|
| 1 | 2 | 7.5 | 4 | 2 |
| 2 | 4 | 15 | 8 | 4 |
| 3 | 6 | 22.5 | 12 | 6 |
| 4 | 8 | 30 | 16 | 8 |



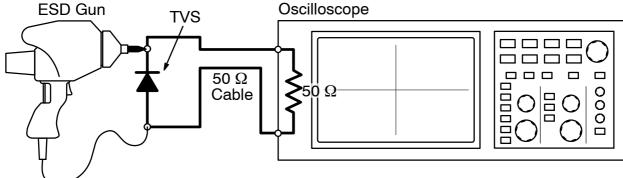


Figure 14. Diagram of ESD Test Setup

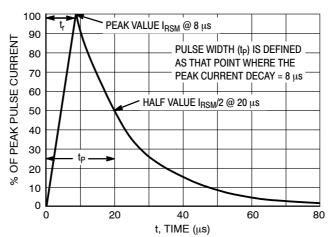


Figure 15. 8 x 20 μs Pulse Waveform

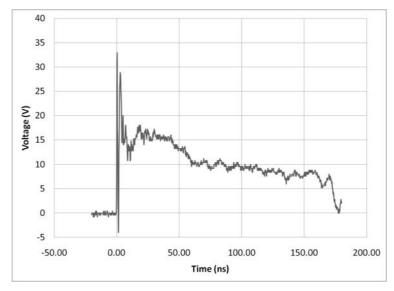


Figure 16. ESD Clamping Voltage +8 kV per IEC6100-4-2 (external to internal pin)

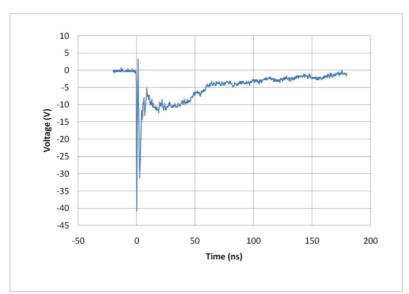


Figure 17. ESD Clamping Voltage -8 kV per IEC6100-4-2 (external to internal pin)

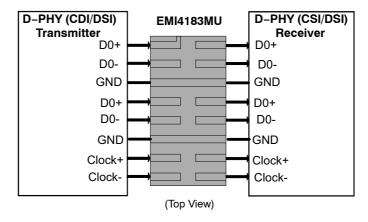


Figure 18. EMI4183MU MIPI D-PHY Application Diagram

DETAIL A

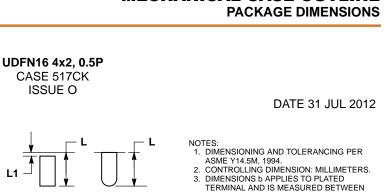
BOTTOM VIEW

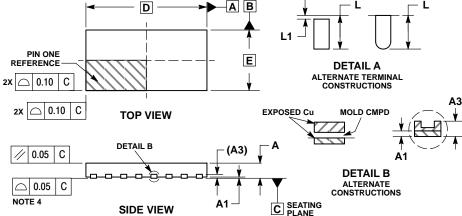
e

e/2

SCALE 4:1

0.10 MIN



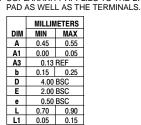


12X L

0.10 M C A B

0.05 M C NOTE 3

14X b



0.15 AND 0.30 MM FROM TERMINAL TIP.
COPLANARITY APPLIES TO THE EXPOSED

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

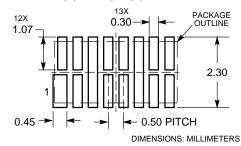
M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " •", may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT



| DOCUMENT NUMBER: | 98AON82418E | Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | | |
|------------------|------------------|--|-------------|--|
| DESCRIPTION: | UDFN16 4X2, 0.5P | | PAGE 1 OF 1 | |

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.org/www.onsemi.or

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

